

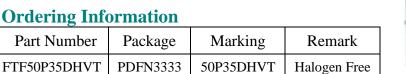
### **Dual P-Channel 350V Enhancement Mode MOSFETs**

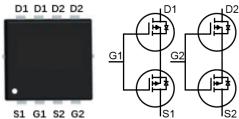
#### **General Features**

- Proprietary Advanced Planar Technology
- Rugged Polysilicon Gate Cell Structure
- Proprietary Advanced High Vth Technology
- ➤ RoHS Compliant
- ➤ Halogen-free available

BV <sub>DSS</sub>	RDS(ON) (Max.)	$I_D$
-350V	50 Ω	-0.5A

#### PDFN3333





## **Absolute Maximum Ratings**

 $T_A=25\,^{\circ}\text{C}$  unless otherwise specified

Symbol	Parameter	FTF50P35DHVT	Unit	
$V_{ m DSS}$	Drain-to-Source Voltage <sup>[1]</sup>	-350	V	
$I_D$	Continuous Drain Current	-0.5	Δ.	
$I_{DM}$	Pulsed Drain Current <sup>[2]</sup>	-2.0	A	
$P_D$	Power Dissipation	16	W	
$V_{GS}$	Gate-to-Source Voltage	±20	V	
$T_{ m L}$	Soldering Temperature Distance of 1.6mm from case for 10 seconds	300	°C	
T <sub>J</sub> and T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to 150		

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.

### **Thermal Characteristics**

Symbol	Parameter	FTF50P35DHVT	Unit
$R_{ heta JA}$	Thermal Resistance, Junction-to-Ambient	34	K/W



### **Electrical Characteristics**

#### **OFF** Characteristics

 $T_A = 25$ °C unless otherwise specified

Symbol	Parameter	Min.	Тур.	Max.	Unit	Test Conditions
BV <sub>DSS</sub>	Drain-to-Source Breakdown Voltage	-350			V	V <sub>GS</sub> =0V, I <sub>D</sub> =-250μA
$I_{ m DSS}$	Drain-to-Source Leakage Current			-1	μΑ	$V_{DS} = -350V$ , $V_{GS} = 0V$
				-100	μΑ	$V_{DS}$ =-350V, $V_{GS}$ = 0V $T_J$ =125°C
$I_{GSS}$	Gate-to-Source Leakage Current			1	μΑ	$V_{GS} = +20V, V_{DS} = 0V$
				-1		V <sub>GS</sub> =-20V, V <sub>DS</sub> =0V

#### **ON** Characteristics

#### $T_A = 25$ °C unless otherwise specified

Symbol	Parameter	Min.	Тур.	Max.	Unit	Test Conditions
R <sub>DS(ON)</sub>	Static Drain-to-Source On-Resistance		25	50	Ω	$V_{GS}$ =-10V, $I_D$ =-50mA <sup>[3]</sup>
$V_{\text{GS(TH)}}$	Gate Threshold Voltage	-2		-5	V	$V_{GD} = 0V, I_D = -250 \mu A$
V <sub>GS(TH)_REV</sub>	Reverse Gate Threshold Voltage	-5		-10	V	$V_{GS} = 0V$ , $I_D = 5\mu A$

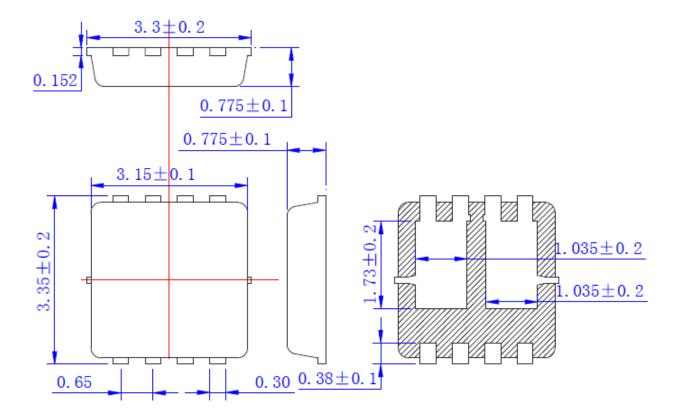
#### NOTE:

- [1]  $T_J = +25$ °C to +150°C
- [2] Repetitive rating, pulse width limited by maximum junction temperature.
- [3] Pulse width \( 380\mu s; \) duty cycle \( \le 2\% \).



# **Package Dimensions**

### **PDFN3333**





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